

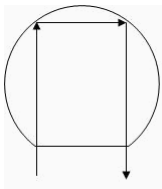
Part Number

Customer

Category	Parameter	Specification	Measurement Method
OverallWafer	1.0	Diameter	150.00 +/- 0.20 mm
	2.0	Primary Flat Orientation	{110} +/- 1.0 degree
	3.0	Primary Flat Length	57.50 +/- 2.50 mm
	4.0	Secondary Flat Orientation	none
	5.0	Overall Thickness	406.50 +/- 6.00 µm
	6.0	Total Thickness Variation (TTV)	<3.00µm
	7.0	Bow	<60.00µm
	8.0	Warp	<60.00µm
	9.0	Edge Chips	0
	10.0	Edge Exclusion	5mm
	11.0	Bond Process	Fusion Bonding
HandleSilicon	12.0	Handle Growth Method	CZ
	13.0	Handle Orientation	{100} +/- 0.5 degree
	14.0	Handle Thickness	400.00 +/- 5.00 µm
	15.0	Handle Doping Type	P
	16.0	Handle Dopant	Boron
	17.0	Handle Resistivity	1~20 Ohmcm
	18.0	Backside Finish	Polished with oxide, lasermark, and light handling marks
BuriedOxide	19.0	Oxide Type	Thermal
	20.0	Oxide Thickness	5,000.00 +/- 250.00 A
	21.0	Oxide formed on	Handle or/and Device
DeviceSilicon	22.0	Device Growth Method	CZ
	23.0	Device Orientation	{100} +/- 0.5 degree
	24.0	Nominal Thickness	6.00 +/- 0.50 µm
	25.0	Distance to device silicon edge from wafer edge	< 2mm
	26.0	Device Doping Type	N
	27.0	Device Dopant	Phosphorous
	28.0	Device Resistivity	0.4~1.15 Ohmcm
	29.0	Surface Voids	None
	30.0	Haze	None
	31.0	Scratches	none on the front-side

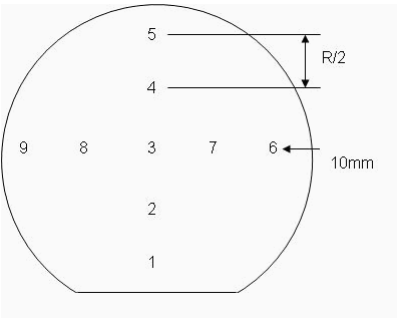
Part Number	Customer
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Category	Parameter	Specification	Measurement Method
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Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 150.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	
Explanatory Notes	1. Microscope inspection performed using microscope scan as below. 5x objective.		

2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information